



#9/Suppl. S  
Amend B  
6.25.02  
PATENT APPLICATION *C. Wells*

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q61741

Takashi UDAGAWA

Appln. No.: 09/881,782

Group Art Unit: 2815

Confirmation No.: 1610

Examiner: Paul E. Brock II

Filed: June 18, 2001

RECEIVED  
JUN 21 2002  
TECHNOLOGY CENTER 2800

For: GROUP-III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE, LIGHT EMITTING DIODE LAMP, LIGHT SOURCE, ELECTRODE FOR GROUP-III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE, AND METHOD FOR PRODUCING THE ELECTRODE

SUPPLEMENTAL AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

Sir:

Supplemental to the Amendment Under 37 C.F.R. § 1.111 filed June 14, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please enter the following amended claims:

*new C6*  
*B.I.*  
21. (Amended) A group-III nitride semiconductor light-emitting diode comprising at least a first conduction-type single crystal substrate provided with a first conduction-type back-surface ohmic electrode on a back surface thereof, a buffer layer comprising a boron phosphide (BP)-based material on a front surface of said single crystal substrate, a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of hetero-junction structure on said buffer layer, and a window layer comprising an electrically conducting transparent oxide crystal